

UNITED STATES PATENT AND TRADEMARK OFFICE
CERTIFICATE OF CORRECTION

PATENT NO. : 7,718,987 B2
APPLICATION NO. : 10/589915
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INVENTOR(S) : Tow Chong Chong et al.

Page 1 of 1

It is certified that error appears in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

Col 10, claim 13, lines 26–31, delete “structures; and
a second contact wherein said crystallization temperature of said phase change material
of said initial layer and said phase change material of said final layer is in a range from
about 90 degrees Celsius to about 120 degrees Celsius formed over said final layer.”

and insert:

--structures, wherein said crystallization temperature of said phase change material of
said initial layer and said phase change material of said final layer is in a range from
about 90 degrees Celsius to about 120 degrees Celsius; and
a second contact formed over said final layer.--

Signed and Sealed this

Nineteenth Day of October, 2010

A handwritten signature in black ink, reading "David J. Kappos". The signature is written in a cursive, flowing style with a large, stylized "D" and "K".

David J. Kappos
Director of the United States Patent and Trademark Office